# MSKSEMI 美森科







TVS



TCC



MOV



GDT



PIFF

# **ST2045-MS**

Product specification





## **FEATURES**

- Excellent high temperature stability
- Low forward voltage
- Low power loss/ high efficiency
- High forward surge capability
- Ideal for automated placement
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

#### **MECHANICAL DATA**

Case: TO-277
Molding compound meets UL 94 V-0 flammability rating Moisture sensitivity level: level 1, per J-STD-020

■ **Terminal:** Matte tin plated leads, solderable per JESD22-B102

Meet JESD 201 class 2 whisker test

Polarity: Indicated by cathode band

• Weight: 0.095g (approximately)

## **TYPICAL APPLICATIONS**

Schottky barrier rectifier is designed for high frequency miniature switched mode power supplies such as adapters, lighting and on-board DC/DC converters.

#### **Reference News**

TO-277	PIN CONFIGURATION	MARKING	
	Cathode Anode 1 & Heatsink  Anode 2	MSKSEMI ST2045L	



## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER			SYMBOL	SB2045L	UNIT
Maximum repetitive peak reverse voltage			V <sub>RRM</sub>	45	V
Maximum average forward rectified current			I <sub>F(AV)</sub>	20	Α
Peak forward surge current, 8.3 ms singlehalf sine-wave superimposed on rated load per diode			I <sub>FSM</sub>	250	А
Maximum instantaneous forward voltage per diode (Note 1)	I <sub>F</sub> = 20A	T <sub>J</sub> = 25°C	V <sub>F</sub>	0.55	V
Maximum instantaneous reverse current per diode at rated reverse voltage $T_J = 25^{\circ}C$		I <sub>R</sub>	100	μA	
Typical thermal resistance			$R_{\theta JL}$	11	°C/W
Operating temperature range			TJ	- 55 to +150	°C
Storage temperature range			T <sub>STG</sub>	- 55 to +150	°C

Note 1: Pulse Test with Pulse Width=300µs, 1% Duty Cycle



## RATINGS AND CHARACTERISTICS CURVES (T<sub>A</sub>=25°C unless otherwise noted)

#### FIG.1 FORWARD CURRENT DERATING CURVE

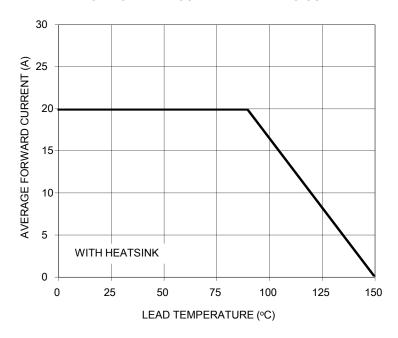
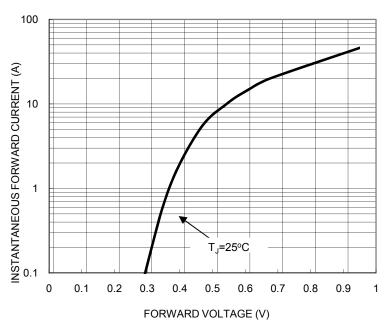


FIG. 2 TYPICAL FORWARD CHARACTERISTICS





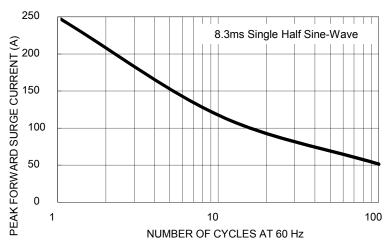


FIG. 4 TYPICAL REVERSE CHARACTERISTICS

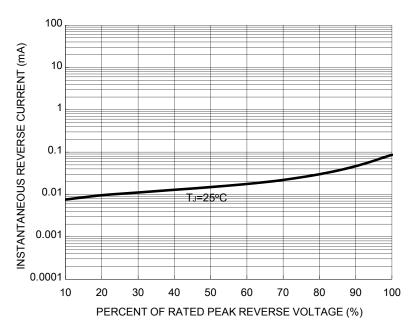
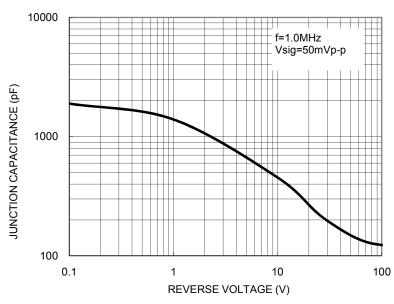
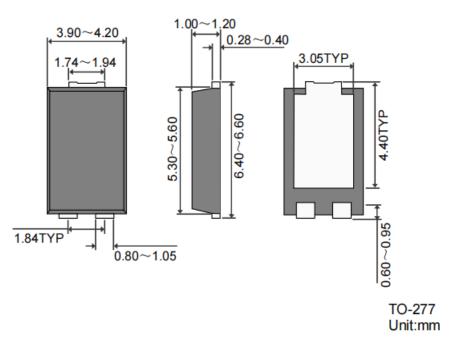


FIG. 5 TYPICAL JUNCTION CAPACITANCE

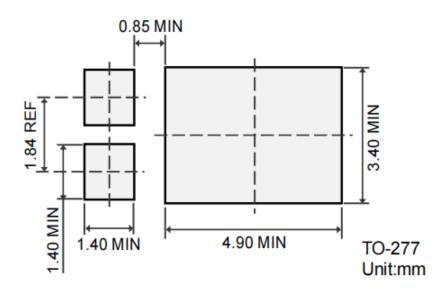




## **Package Outline Dimensions**



# **Suggested Solder Pad Layout**



## **REEL SPECIFICATION**

P/N	PKG	QTY
ST2045-MS	TO-277	5000



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